

### **isc** Silicon NPN Power Transistor

# INCHANGE SEMICONDUCTOR

## 2SD2374A

#### DESCRIPTION

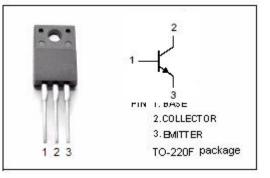
- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V(Min)
- Collector Power Dissipation-:  $P_C$ = 25 W@ T<sub>C</sub>= 25 °C
- Low Collector Saturation Voltage : V<sub>CE(sat)</sub>= 1.2V(Max)@ (I<sub>C</sub>= 3A, I<sub>B</sub>= 0.375A)
- Complement to Type 2SB1548A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

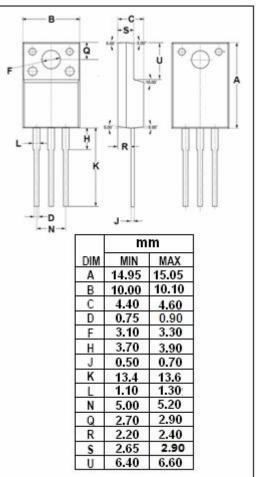
### **APPLICATIONS**

• Designed for power amplifications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
lc	Collector Current-Continuous	3	А
Ісм	Collector Current-Peak	5	А
Pc	Collector Power Dissipation @Ta=25℃	2	
	Collector Power Dissipation @T <sub>C</sub> =25°C	25	W
TJ	Junction Temperature	ēmperature 150	
T <sub>stg</sub>	Storage Temperature	-55~150	°C







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### ELECTRICAL CHARACTERISTICS

#### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.375A			1.2	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V			1.8	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 80V; V <sub>BE</sub> = 0			200	μA
Iceo	Collector Cutoff Current	V <sub>CE</sub> = 60V; I <sub>B</sub> = 0			300	μ <b>Α</b>
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	70		250	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	10			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A;V <sub>CE</sub> = 10V; f <sub>test</sub> = 10MHz		30		MHz

Q	Р	
70-150	120-250	

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